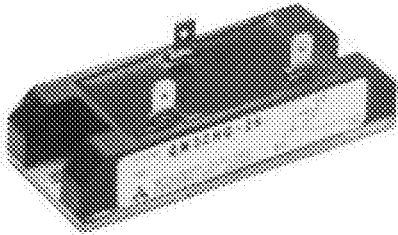


QM30HQ-24

DRIVE USE FOR HIGH POWER TRANSISTOR
INSULATED TYPE

QM30HQ-24



- **I_C** Collector current **30A**
- **V_{CEX}** Collector-emitter voltage **1200V**
- **h_{FE}** DC current gain..... **5**
- **Insulated Type**
- **UL Recognized**

Yellow Card No. E80276 (N)

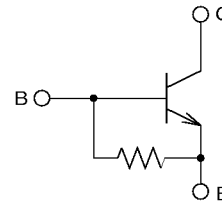
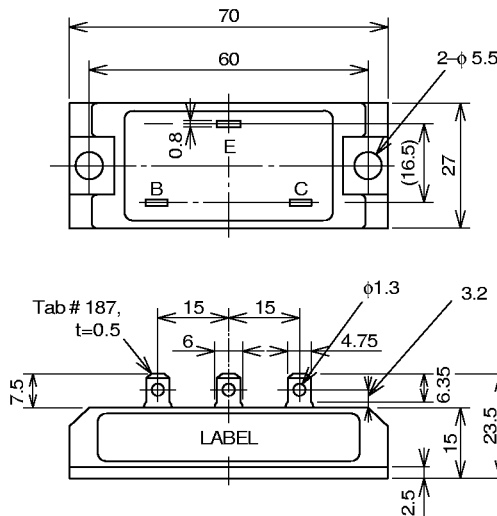
File No. E80271

APPLICATION

Base driver for High voltage transistor modules

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



QM30HQ-24

DRIVE USE FOR HIGH POWER TRANSISTOR
INSULATED TYPE

ABSOLUTE MAXIMUM RATINGS (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CEX(SUS)}	Collector-emitter voltage	I _C =1A, V _{EB} =2V	1200	V
V _{CEX}	Collector-emitter voltage	V _{EB} =2V	1200	V
V _{CB0}	Collector-base voltage	Emitter open	1200	V
V _{EB0}	Emitter-base voltage	Collector open	7	V
I _C	Collector current	DC	30	A
P _C	Collector dissipation	T _C =25°C	310	W
I _B	Base current	DC	6	A
T _J	Junction temperature		-40~+150	°C
T _{stg}	Storage temperature		-40~+125	°C
V _{iso}	Isolation voltage	Charged part to case, AC for 1 minute	2500	V
—	Mounting torque	Mounting screw M5	1.47~1.96	N·m
—			15~20	kg·cm
—	Weight	Typical value	90	g

ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise noted)

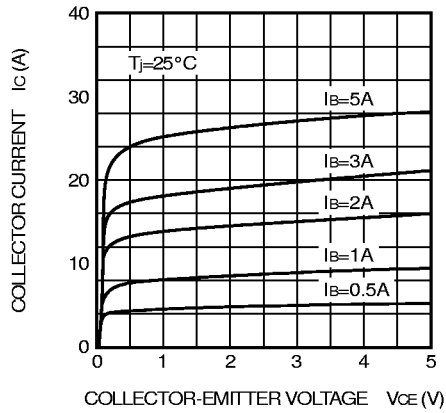
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{CEX}	Collector cutoff current	V _{CE} =1200V, V _{EB} =2V	—	—	1.0	mA
I _{CB0}	Collector cutoff current	V _{CB} =1200V, Emitter open	—	—	1.0	mA
I _{EB0}	Emitter cutoff current	V _{EB} =7V	—	—	200	mA
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =15A, I _B =3A	—	—	1.0	V
V _{BE(sat)}	Base-emitter saturation voltage		—	—	1.5	V
h _{FE}	DC current gain	I _C =15A, V _{CE} =1V	5	—	—	—
t _{on}	Switching time	V _{CC} =600V, I _C =15A, I _{B1} =-I _{B2} =3A	—	—	1.5	μs
t _s			—	—	7.0	μs
t _f			—	—	2.0	μs
R _{th(j-c) Q}	Thermal resistance (junction to case)	Transistor part	—	—	0.4	°C/W
R _{th(c-f)}	Contact thermal resistance (case to fin)	Conductive grease applied	—	—	0.25	°C/W

QM30HQ-24

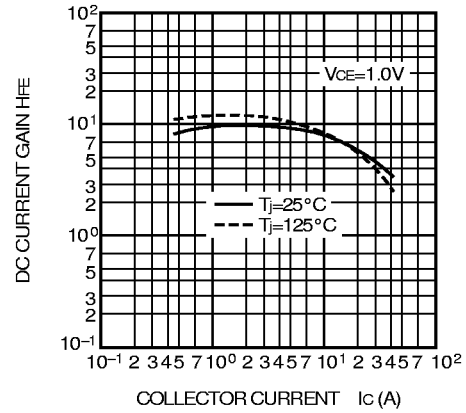
DRIVE USE FOR HIGH POWER TRANSISTOR
INSULATED TYPE

PERFORMANCE CURVES

COMMON EMITTER OUTPUT
CHARACTERISTICS (TYPICAL)



DC CURRENT GAIN VS.
COLLECTOR CURRENT (TYPICAL)



SATURATION VOLTAGE
CHARACTERISTICS (TYPICAL)

